3rd Research Coordination Meeting Ion Beam Induced Spatio-Temporal Structural Evolution of Materials: Accelerators for a New Technology Era, CRP No: F11020







Contribution ID: 6

Type: not specified

## CREATION OF SILICON VACANCY IN SILICON CARBIDE USING PROTON BEAM WRITING

Monday, 25 April 2022 11:50 (20 minutes)

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Session Classification: Session 1: Laboratory Reports